



# MBRF30100CT thru MBRF30200CT

**30.0A Schottky Barrier Rectifiers**

Rectifier Reverse Voltage 100 to 200V

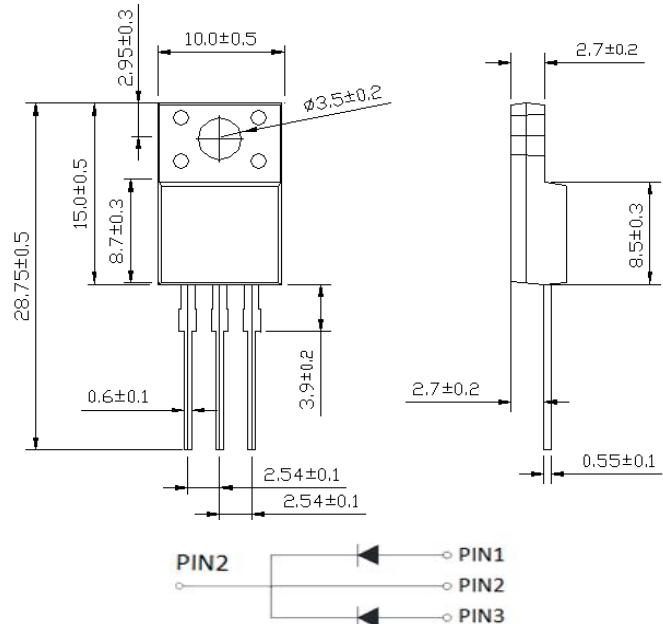
**ITO-220AB**

## Features

- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Solder dip 260 °C max. 8 s, per JESD 22-B106

## Mechanical Data

- **Package:** ITO-220AB  
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant
- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD22-B102
- **Polarity:** As marked



Dimensions in millimeters ( 1mm =0.0394" )

## ■Maximum Ratings ( $T_a=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBRF30100CT	MBRF30150CT	MBRF30200CT
Device marking code			MBRF30100CT	MBRF30150CT	MBRF30200CT
Repetitive Peak Reverse Voltage	$V_{RRM}$	V	100	150	200
Average Rectified Output Current @60Hz sine wave, R-load, $T_a=25^\circ\text{C}$	$I_O$	A		30	
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, $T_a=25^\circ\text{C}$	$I_{FSM}$	A		180	
Current Squared Time @ $1\text{ms} \leq t < 8.3\text{ms}$ $T_j=25^\circ\text{C}$ ,	$I^2t$	$\text{A}^2\text{s}$		134	
Storage Temperature	$T_{stg}$	°C		-55 ~ +175	
Junction Temperature	$T_j$	°C		-55 ~ +150	

## ■Electrical Characteristics ( $T_a=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBRF30100CT	MBRF30150CT	MBRF30200CT
Maximum instantaneous forward voltage drop per diode	$V_{FM}$	V	$I_{FM}=15.0\text{A}$	0.87	0.93	0.95
Maximum DC reverse current at rated DC blocking voltage per diode	$I_{RRM1}$	mA	$V_{RM}=V_{RRM}$ $T_a=25^\circ\text{C}$	0.15	20	0.1
	$I_{RRM2}$		$V_{RM}=V_{RRM}$ $T_a=125^\circ\text{C}$			
Thermal Resistance	Between junction and case		$R_{\theta J-C}$	$^\circ\text{C/W}$		2.0

**Rating and Characteristic Curves (  $T_A=25^\circ\text{C}$  Unless otherwise noted )**  
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